

# PSMN7R6-60BS

# N-channel 60 V 7.8 m $\Omega$ standard level MOSFET in D2PAK Rev. 2 — 2 March 2012 Product data

Product data sheet

#### **Product profile** 1.

## 1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

## 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol               | Parameter                                          | Conditions                                                                                                             | Min | Тур  | Max | Unit |
|----------------------|----------------------------------------------------|------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| $V_{DS}$             | drain-source voltage                               | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C                                                                        | -   | -    | 60  | V    |
| I <sub>D</sub>       | drain current                                      | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>                                                                 | -   | -    | 92  | Α    |
| P <sub>tot</sub>     | total power dissipation                            | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>                                                                           | -   | -    | 149 | W    |
| Tj                   | junction temperature                               |                                                                                                                        | -55 | -    | 175 | °C   |
| Static charact       | eristics                                           |                                                                                                                        |     |      |     |      |
| R <sub>DSon</sub>    | drain-source on-state resistance                   | $V_{GS} = 10 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 13; see Figure 9                   | -   | 5.9  | 7.8 | mΩ   |
| Dynamic char         | acteristics                                        |                                                                                                                        |     |      |     |      |
| $Q_{GD}$             | gate-drain charge                                  | $V_{GS} = 10 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; see <u>Figure 15</u> ; see <u>Figure 14</u> | -   | 10.6 | -   | nC   |
| Q <sub>G(tot)</sub>  | total gate charge                                  | $V_{GS} = 10 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u> | -   | 38.7 | -   | nC   |
| Avalanche rug        | gedness                                            |                                                                                                                        |     |      |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source<br>avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 92 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 $\Omega$ ; unclamped            | -   | -    | 110 | mJ   |



## 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1   | G      | gate                              |                    | <u>_</u>       |
| 2   | D      | drain[1]                          | mb                 | D D            |
| 3   | S      | source                            |                    |                |
| mb  | D      | mounting base; connected to drain | 1 3                | mbb076 S       |
|     |        |                                   | SOT404 (D2PAK)     |                |

<sup>[1]</sup> It is not possible to make connection to pin 2.

## 3. Ordering information

Table 3. Ordering information

| Type number  | Package |                                                                                  |         |
|--------------|---------|----------------------------------------------------------------------------------|---------|
|              | Name    | Description                                                                      | Version |
| PSMN7R6-60BS | D2PAK   | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                    | Conditions                                                                                                    | Min | Max | Unit |
|----------------------|----------------------------------------------|---------------------------------------------------------------------------------------------------------------|-----|-----|------|
| $V_{DS}$             | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C                                                               | -   | 60  | V    |
| $V_{DGR}$            | drain-gate voltage                           | $R_{GS} = 20 \text{ k}\Omega$                                                                                 | -   | 60  | V    |
| $V_{GS}$             | gate-source voltage                          |                                                                                                               | -20 | 20  | V    |
| I <sub>D</sub>       | drain current                                | $V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$           | -   | 65  | Α    |
|                      |                                              | $V_{GS} = 10 \text{ V}$ ; $T_{mb} = 25 \text{ °C}$ ; see <u>Figure 1</u>                                      | -   | 92  | Α    |
| $I_{DM}$             | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ;<br>see Figure 3                                               | -   | 389 | Α    |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>                                                                  | -   | 149 | W    |
| T <sub>stg</sub>     | storage temperature                          |                                                                                                               | -55 | 175 | °C   |
| T <sub>j</sub>       | junction temperature                         |                                                                                                               | -55 | 175 | °C   |
| T <sub>sld(M)</sub>  | peak soldering temperature                   |                                                                                                               | -   | 260 | °C   |
| Source-drai          | in diode                                     |                                                                                                               |     |     |      |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C                                                                                       | -   | 92  | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$                                                      | -   | 389 | Α    |
| Avalanche i          | ruggedness                                   |                                                                                                               |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 92 A; $V_{sup} \le$ 100 V; $R_{GS}$ = 50 $\Omega$ ; unclamped | -   | 110 | mJ   |
|                      |                                              |                                                                                                               |     |     |      |

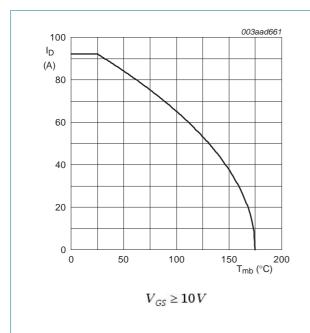


Fig 1. Continuous drain current as a function of mounting base temperature

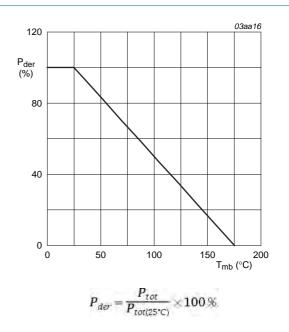
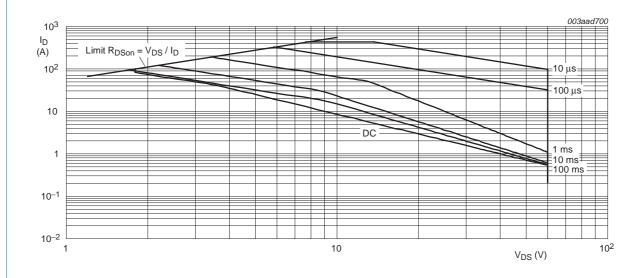


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25 \, {}^{\circ}C; I_{DM}$  is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol               | Parameter                                         | Conditions                                            | Min | Тур  | Max  | Unit |
|----------------------|---------------------------------------------------|-------------------------------------------------------|-----|------|------|------|
| $R_{th(j-mb)}$       | thermal resistance from junction to mounting base | see Figure 4                                          | -   | 0.49 | 1.01 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient       | Minimum footprint; mounted on a printed circuit board | -   | 50   | -    | K/W  |

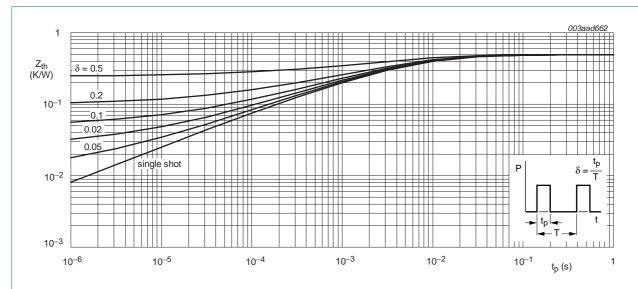


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

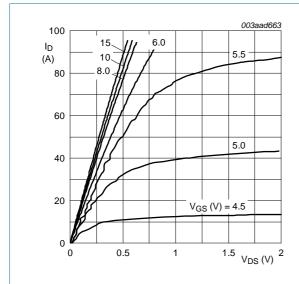
## **Characteristics**

Table 6. Characteristics

| Table 6.                                         | Characteristics                   |                                                                                                                                                   |     |      |     |      |
|--------------------------------------------------|-----------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| Symbol                                           | Parameter                         | Conditions                                                                                                                                        | Min | Тур  | Max | Unit |
| Static cha                                       | aracteristics                     |                                                                                                                                                   |     |      |     |      |
| $V_{(BR)DSS}$                                    | drain-source                      | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$                                                                                                     | 54  | -    | -   | V    |
|                                                  | breakdown voltage                 | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                                                                                                      | 60  | -    | -   | V    |
| $V_{GS(th)}$                                     | gate-source threshold voltage     | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C;<br>see <u>Figure 10</u> ; see <u>Figure 11</u>                                                   | 2   | 3    | 4   | V    |
| $V_{GSth}$                                       | gate-source threshold voltage     | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C;<br>see <u>Figure 11</u>                                                                       | 1   | -    | -   | V    |
|                                                  |                                   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see <u>Figure 11</u>                                                                            | -   | -    | 4.6 | V    |
| I <sub>DSS</sub>                                 | drain leakage current             | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                                                                | -   | 0.05 | 10  | μΑ   |
|                                                  |                                   | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$                                                                               | -   | -    | 100 | μΑ   |
| I <sub>GSS</sub>                                 | gate leakage current              | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                                                                | -   | 2    | 100 | nΑ   |
|                                                  |                                   | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                                                               | -   | 2    | 100 | nΑ   |
| R <sub>DSon</sub> drain-source on-<br>resistance | drain-source on-state resistance  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12                                                            | -   | 13.3 | 18  | mΩ   |
|                                                  |                                   | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$<br>see Figure 13; see Figure 9                                            | -   | 5.9  | 7.8 | mΩ   |
| R <sub>G</sub>                                   | gate resistance                   | f = 1 MHz                                                                                                                                         | -   | 0.98 | -   | Ω    |
| Dynamic                                          | characteristics                   |                                                                                                                                                   |     |      |     |      |
| Q <sub>G(tot)</sub>                              | total gate charge                 | $I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$                                                                               | -   | 38.7 | -   | nC   |
| Q <sub>GS</sub>                                  | gate-source charge                | see Figure 14; see Figure 15                                                                                                                      | -   | 12.9 | -   | nC   |
| Q <sub>GS(th)</sub>                              | pre-threshold gate-source charge  |                                                                                                                                                   | -   | 6.9  | -   | nC   |
| Q <sub>GS(th-pl)</sub>                           | post-threshold gate-source charge |                                                                                                                                                   | -   | 6    | -   | nC   |
| $Q_{GD}$                                         | gate-drain charge                 | $I_D = 25 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 15</u> ; see <u>Figure 14</u>                            | -   | 10.6 | -   | nC   |
| $V_{GS(pl)}$                                     | gate-source plateau<br>voltage    | $I_D = 25 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>                                                      | -   | 5.6  | -   | V    |
| C <sub>iss</sub>                                 | input capacitance                 | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 8}}$ | -   | 2651 | -   | pF   |
| C <sub>oss</sub>                                 | output capacitance                | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{}$               | -   | 342  | -   | pF   |
| C <sub>rss</sub>                                 | reverse transfer capacitance      | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 8}}$ | -   | 183  | -   | pF   |
| t <sub>d(on)</sub>                               | turn-on delay time                | $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$                                                                                 | -   | 19   | -   | ns   |
| t <sub>r</sub>                                   | rise time                         | $R_{G(ext)} = 4.7 \Omega$                                                                                                                         | -   | 21   | -   | ns   |
| t <sub>d(off)</sub>                              | turn-off delay time               |                                                                                                                                                   | -   | 37   | -   | ns   |
| t <sub>f</sub>                                   | fall time                         |                                                                                                                                                   | -   | 13   | -   | ns   |

Table 6. Characteristics ... continued

| Symbol             | Parameter             | Conditions                                                                                                      | Min | Тур  | Max | Unit |
|--------------------|-----------------------|-----------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| Source-drain diode |                       |                                                                                                                 |     |      |     |      |
| V <sub>SD</sub>    | source-drain voltage  | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>                     | -   | 0.86 | 1.2 | V    |
| t <sub>rr</sub>    | reverse recovery time | $I_S = 25 \text{ A}$ ; $dI_S/dt = 100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 30 \text{ V}$ | -   | 40.4 | -   | ns   |
| Q <sub>r</sub>     | recovered charge      |                                                                                                                 | -   | 56   | -   | nC   |



 $T_i = 25$  °C;  $t_p = 300 \, \mu s$ 

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

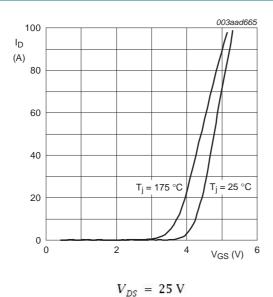


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

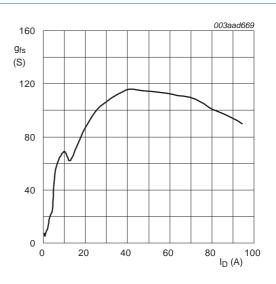
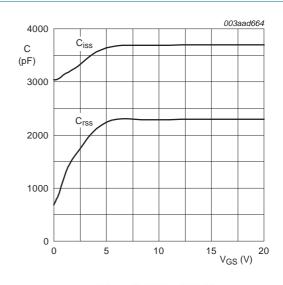


Fig 6. Forward transconductance as a function of drain current; typical values



 $V_{DS} = 0 \text{ V; } f = 1 \text{ MHz}$ 

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

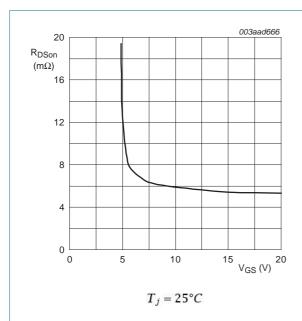
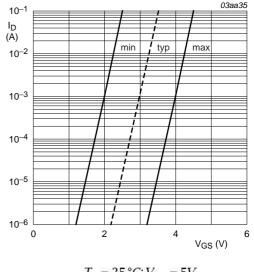


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$ 

Fig 10. Sub-threshold drain current as a function of gate-source voltage

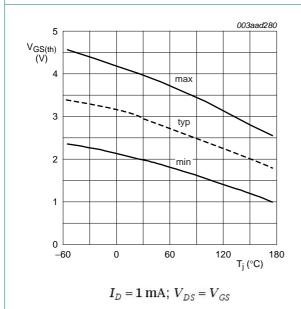


Fig 11. Gate-source threshold voltage as a function of junction temperature

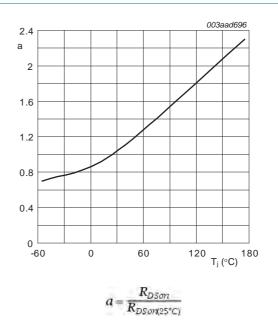


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

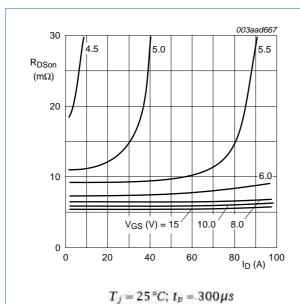
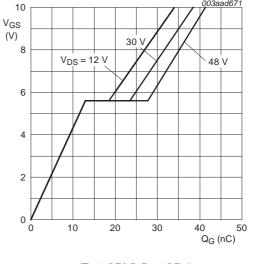


Fig 13. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25^{\circ}C; I_D = 25 A$ 

Fig 14. Gate-source voltage as a function of gate charge; typical values

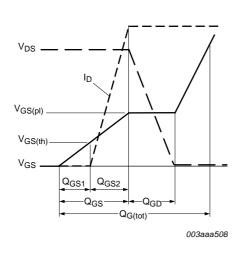
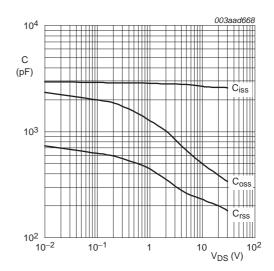


Fig 15. Gate charge waveform definitions



 $V_{DS} = 0V$ ; f = 1 MHz

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

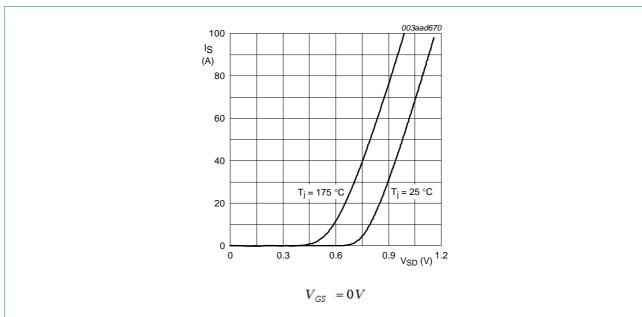


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## 7. Package outline

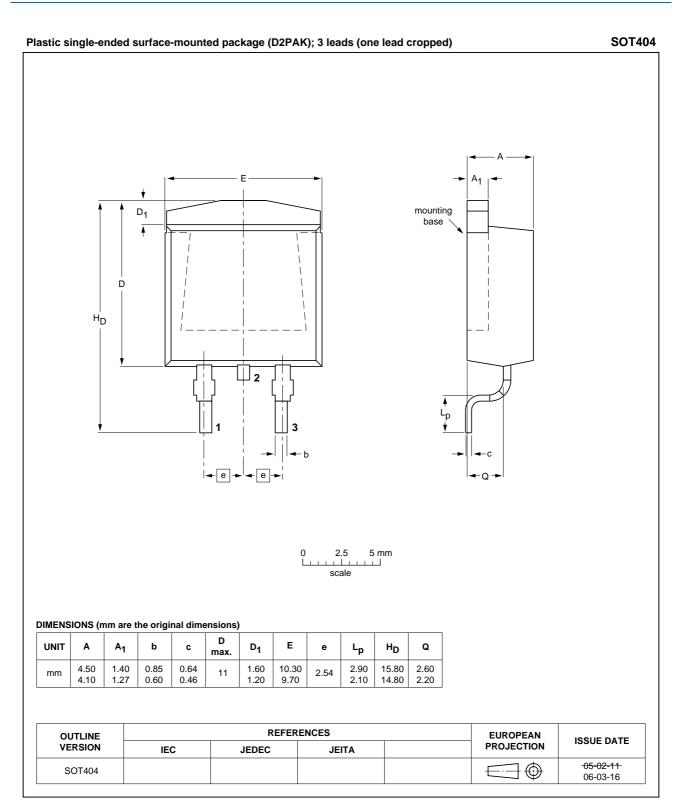


Fig 18. Package outline SOT404 (D2PAK)

## 8. Revision history

## Table 7. Revision history

| Document ID      | Release date                                             | Data sheet status                        | Change notice | Supersedes       |
|------------------|----------------------------------------------------------|------------------------------------------|---------------|------------------|
| PSMN7R6-60BS v.2 | 20120302                                                 | Product data sheet                       | -             | PSMN7R6-60BS v.1 |
| Modifications:   | <ul><li>Status changed</li><li>Various changes</li></ul> | from objective to product. s to content. |               |                  |
| PSMN7R6-60BS v.1 | 20111020                                                 | Objective data sheet                     | -             | -                |

## 9. Legal information

#### 9.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition                                                                            |
|--------------------------------|-------------------|---------------------------------------------------------------------------------------|
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| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

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## PSMN7R6-60BS

#### N-channel 60 V 7.8 mΩ standard level MOSFET in D2PAK

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For sales office addresses, please send an email to:salesaddresses@nexperia.com

## PSMN7R6-60BS

## **Nexperia**

N-channel 60 V 7.8 m $\Omega$  standard level MOSFET in D2PAK

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